

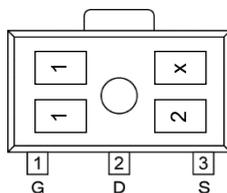
## Power MOSFET

## ■ GENERAL DESCRIPTION

The XP161A1265PR is an N-channel Power MOSFET with low on-state resistance and ultra high-speed switching characteristics. Because high-speed switching is possible, the IC can be efficiently set thereby saving energy. A gate protect diode is built-in to prevent static damage. The small SOT-89 package makes high density mounting possible.

## ■ APPLICATIONS

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

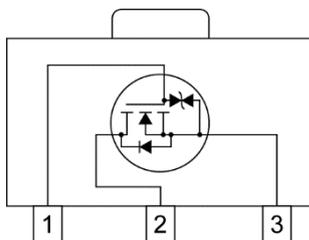
■ PIN CONFIGURATION/  
MARKING

SOT-89  
(TOP VIEW)

\* x represents production lot number.

G : Gate  
S : Source  
D : Drain

## ■ EQUIVALENT CIRCUIT



N-channel MOSFET  
(1 device built-in)

## ■ FEATURES

**Low On-State Resistance** :  $R_{ds(on)}=0.055\ \Omega$  @  $V_{gs}=4.5V$   
:  $R_{ds(on)}=0.095\ \Omega$  @  $V_{gs}=2.5V$

**Ultra High-Speed Switching**

**Gate Protect Diode Built-in**

**Driving Voltage** : 2.5V

**N-Channel Power MOSFET**

**DMOS Structure**

**Package** : SOT-89

## ■ PRODUCT NAME

PRODUCT	PACKAGE	ORDER UNIT
XP161A1265PR-G*	SOT-89	1,000pcs/Reel

(\*) The "-G" suffix denotes Halogen and Antimony free as well as being fully RoHS compliant

## ■ ABSOLUTE MAXIMUM RATINGS

$T_a = 25^\circ\text{C}$			
PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	$V_{dss}$	20	V
Gate-Source Voltage	$V_{gss}$	$\pm 12$	V
Drain Current (DC)	$I_d$	4	A
Drain Current (Pulse)	$I_{dp}$	16	A
Reverse Drain Current	$I_{dr}$	4	A
Channel Power Dissipation *	$P_d$	2	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55~150	$^\circ\text{C}$

\* When implemented on a ceramic PCB (900mm<sup>2</sup> x 0.8mm)

## ELECTRICAL CHARACTERISTICS

### DC Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Drain Cut-Off Current	Idss	Vds=20V, Vgs= 0V	-	-	10	μA
Gate-Source Leak Current	Igss	Vgs= ±12V, Vds= 0V	-	-	±10	μA
Gate-Source Cut-Off Voltage	Vgs(off)	Id= 1mA, Vds= 10V	0.7	-	1.4	V
Drain-Source On-State Resistance*1	Rds(on)	Id= 2A, Vgs= 4.5V	-	0.042	0.055	Ω
		Id= 2A, Vgs= 2.5V	-	0.070	0.095	Ω
Forward Transfer Admittance*1	Yfs	Id= 2A, Vds= 10V	-	8	-	S
Body Drain Diode Forward Voltage	Vf	If= 4A, Vgs= 0V	-	0.85	1.1	V

\*1 Effective during pulse test.

### Dynamic Characteristics

Ta = 25°C

PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Input Capacitance	Ciss	Vds= 10V, Vgs=0V f= 1MHz	-	320	-	pF
Output Capacitance	Coss		-	190	-	pF
Feedback Capacitance	Crss		-	80	-	pF

### Switching Characteristics

Ta = 25°C

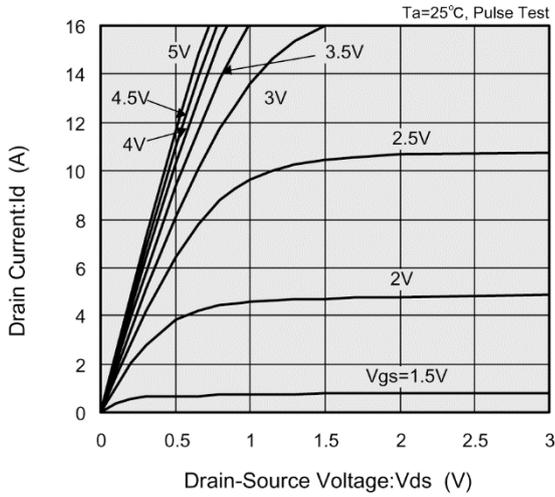
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Turn-On Delay Time	td (on)	Vgs= 5V, Id=2A Vdd= 10V	-	10	-	ns
Rise Time	tr		-	15	-	ns
Turn-Off Delay Time	td (off)		-	55	-	ns
Fall Time	tf		-	40	-	ns

### Thermal Characteristics

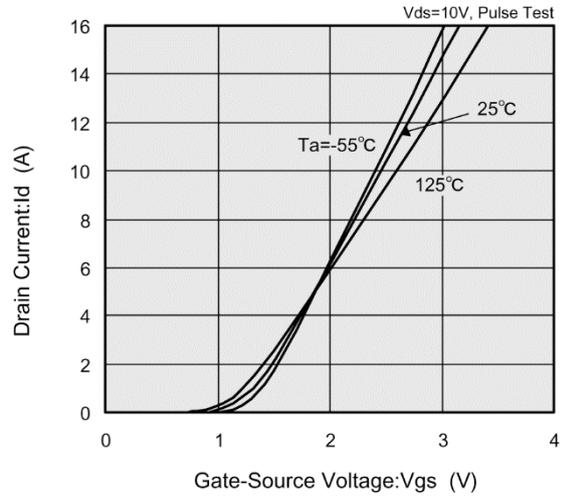
PARAMETER	SYMBOL	CONDITIONS	MIN.	TYP.	MAX.	UNITS
Thermal Resistance (Channel-Ambience)	Rth (ch-a)	Implement on a ceramic PCB	-	62.5	-	°C/W

## TYPICAL PERFORMANCE CHARACTERISTICS

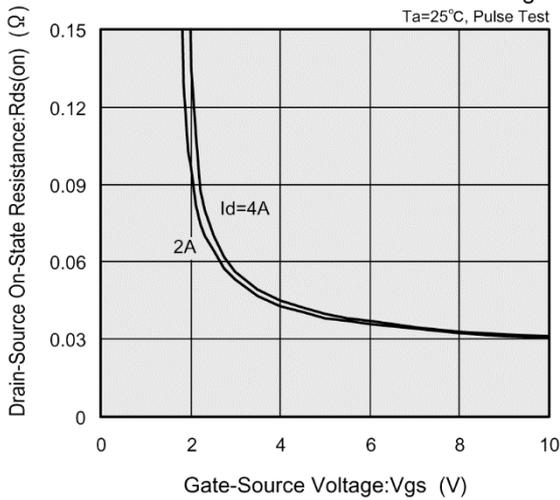
(1) Drain Current vs. Drain-Source Voltage



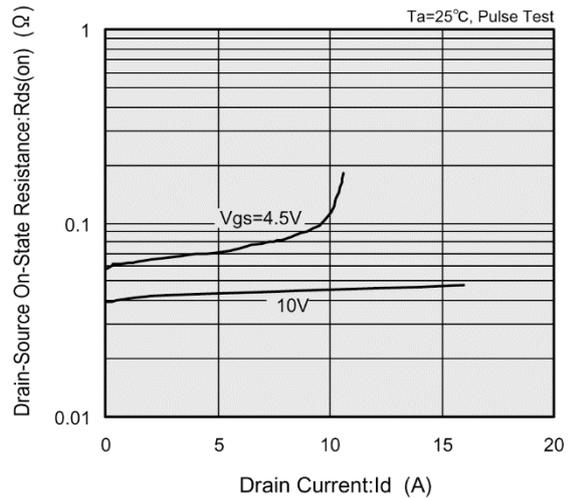
(2) Drain Current vs. Gate-Source Voltage



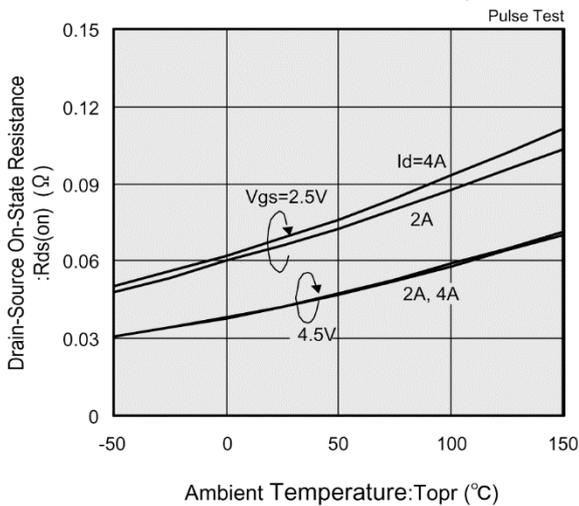
(3) Drain-Source On-State Resistance vs. Gate-Source Voltage



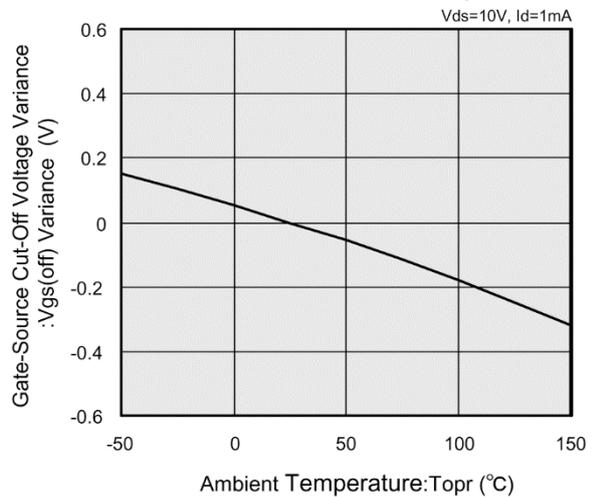
(4) Drain-Source On-State Resistance vs. Drain Current



(5) Drain-Source On-State Resistance vs. Ambient Temperature

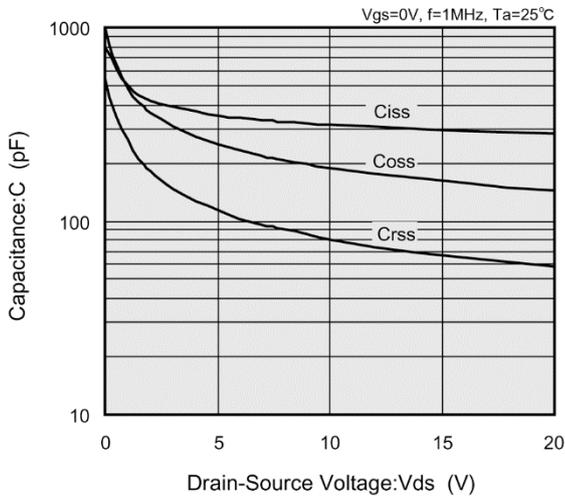


(6) Gate-Source Cut-Off Voltage Variance vs. Ambient Temperature

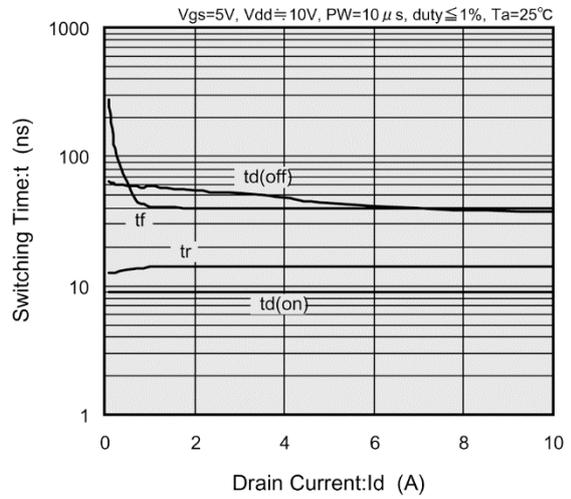


## TYPICAL PERFORMANCE CHARACTERISTICS (Continued)

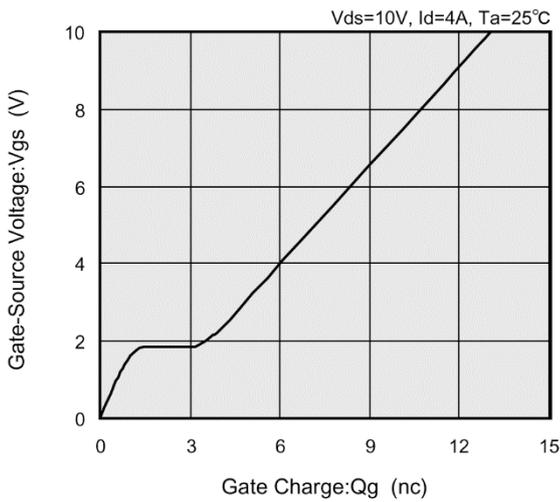
(7) Capacitance vs. Drain-Source Voltage



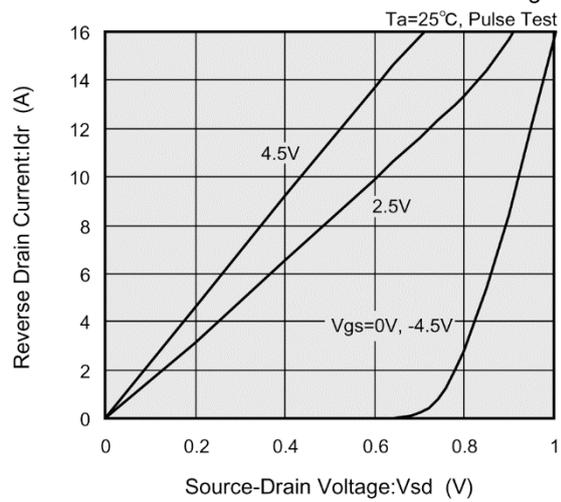
(8) Switching Time vs. Drain Current



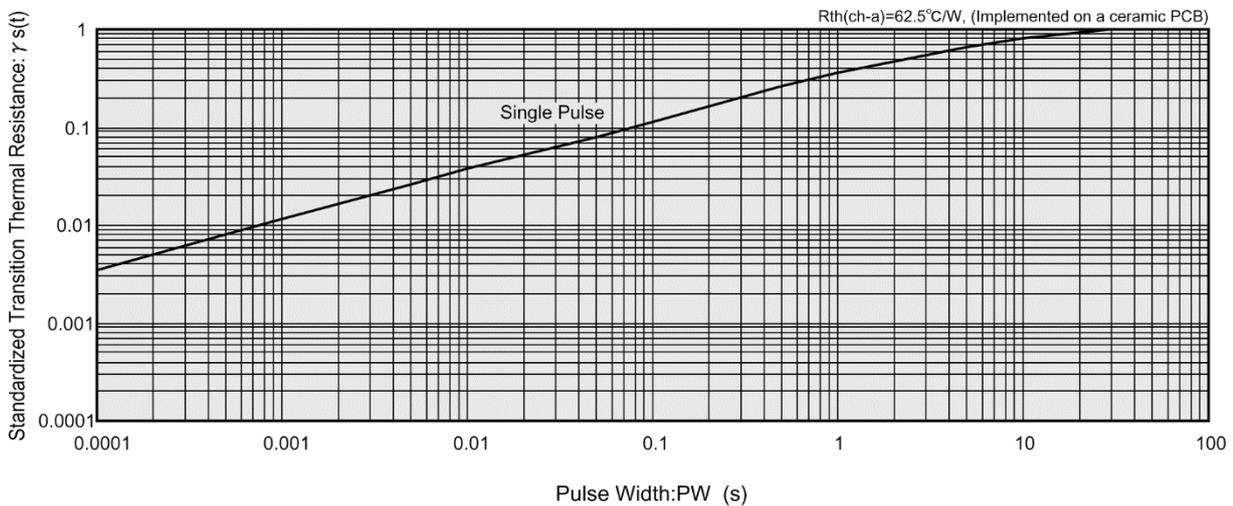
(9) Gate-Source Voltage vs. Gate Charge



(10) Reverse Drain Current vs. Source-Drain Voltage



(11) Standardized transition Thermal Resistance vs. Pulse Width



## ■ PACKAGING INFORMATION

For the latest package information go to, [www.torexsemi.com/technical-support/packages](http://www.torexsemi.com/technical-support/packages)

PACKAGE	OUTLINE / LAND PATTERN	THERMAL CHARACTERISTICS
SOT-89	<a href="#">SOT-89 PKG</a>	<a href="#">SOT-89 Power Dissipation</a>

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